ABSTRACT OF THE DISCLOSURE

When a semiconductor light emitting device or a semiconductor device is produced using a nitride type III-V group compound semiconductor substrate on which a plurality of second regions made of a crystal having a second average dislocation density are regularly arranged in a first region made of a crystal having a first average dislocation density so as to produce the structured substrate, the second average dislocation density being greater than the first average dislocation density being device or an active region of the semiconductor light emitting device or an active region of the semiconductor device is formed in such a manner that it does not pass through any one of the second regions.